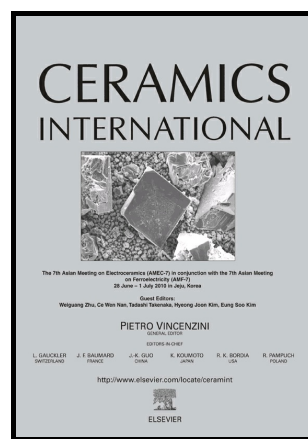


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Abstract

Surface morphological control of the metal-insulator transition behaviors of VO₂ epitaxial thin films is achieved by annealing substrates of (0001)-Al₂O₃ single crystals.

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